



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

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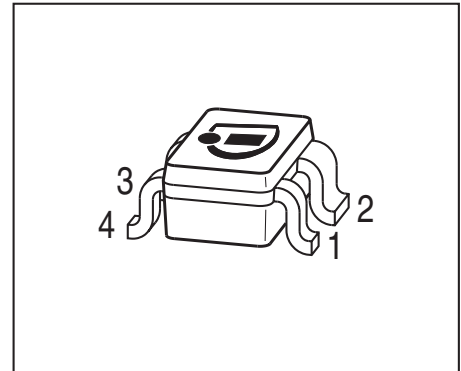
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## High Performance NPN Bipolar RF Transistor

- High performance low noise amplifier
- Low minimum noise figure of typ. 0.8 dB @ 1.8 GHz
- For a wide range of non automotive applications such as WLAN, WiMax, UWB, Bluetooth, GPS, SDARs, DAB, LNB, UMTS/LTE and ISM bands
- Easy to use standard package with visible leads
- Pb-free (RoHS compliant) package



**ESD (Electrostatic discharge) sensitive device, observe handling precaution!**

Type	Marking	Pin Configuration						Package
BF776	R3s	1=B	2=E	3=C	4=E	-	-	SOT343

**Maximum Ratings** at  $T_A = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage $T_A = 25\text{ °C}$ $T_A = -55\text{ °C}$	$V_{CEO}$	4.0 3.5	V
Collector-emitter voltage	$V_{CES}$	13	
Collector-base voltage	$V_{CBO}$	13	
Emitter-base voltage	$V_{EBO}$	1.2	
Collector current	$I_C$	50	mA
Base current	$I_B$	3	
Total power dissipation <sup>1)</sup> $T_S \leq 90\text{ °C}$	$P_{tot}$	200	mW
Junction temperature	$T_J$	150	°C
Ambient temperature	$T_A$	-55 ... 150	
Storage temperature	$T_{Stg}$	-55 ... 150	

### Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>2)</sup>	$R_{thJS}$	$\leq 300$	K/W

<sup>1)</sup>  $T_S$  is measured on the emitter lead at the soldering point to the pcb

<sup>2)</sup> For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC Characteristics</b>					
Collector-emitter breakdown voltage $I_C = 1 \text{ mA}, I_B = 0$	$V_{(BR)CEO}$	4	4.7	-	V
Collector-emitter cutoff current $V_{CE} = 5 \text{ V}, V_{BE} = 0$	$I_{CES}$	-	1	-	nA
Collector-base cutoff current $V_{CB} = 5 \text{ V}, I_E = 0$	$I_{CBO}$	-	1	-	
Emitter-base cutoff current $V_{EB} = 0.5 \text{ V}, I_C = 0$	$I_{EBO}$	-	10	-	
DC current gain $I_C = 30 \text{ mA}, V_{CE} = 3 \text{ V}, \text{ pulse measured}$	$h_{FE}$	-	180	-	-

**Electrical Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>AC Characteristics (verified by random sampling)</b>					
Transition frequency $I_C = 30\text{ mA}$ , $V_{CE} = 3\text{ V}$ , $f = 1\text{ GHz}$	$f_T$	-	46	-	GHz
Collector-base capacitance $V_{CB} = 3\text{ V}$ , $f = 1\text{ MHz}$ , $V_{BE} = 0$ , emitter grounded	$C_{cb}$	-	0.09	-	pF
Collector emitter capacitance $V_{CE} = 3\text{ V}$ , $f = 1\text{ MHz}$ , $V_{BE} = 0$ , base grounded	$C_{ce}$	-	0.25	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$ , $f = 1\text{ MHz}$ , $V_{CB} = 0$ , collector grounded	$C_{eb}$	-	0.5	-	
Noise figure $I_C = 5\text{ mA}$ , $V_{CE} = 3\text{ V}$ , $f = 1.8\text{ GHz}$ , $Z_S = Z_{Sopt}$ $I_C = 5\text{ mA}$ , $V_{CE} = 3\text{ V}$ , $f = 6\text{ GHz}$ , $Z_S = Z_{Sopt}$	$F$	-	0.8 1.3	-	dB
Power gain, maximum stable <sup>1)</sup> $I_C = 30\text{ mA}$ , $V_{CE} = 3\text{ V}$ , $Z_S = Z_{Sopt}$ , $Z_L = Z_{Lopt}$ , $f = 1.8\text{ GHz}$	$G_{ms}$	-	24	-	dB
Power gain, maximum available <sup>1)</sup> $I_C = 30\text{ mA}$ , $V_{CE} = 3\text{ V}$ , $Z_S = Z_{Sopt}$ , $Z_L = Z_{Lopt}$ , $f = 6\text{ GHz}$	$G_{ma}$	-	12.5	-	dB
Transducer gain $I_C = 30\text{ mA}$ , $V_{CE} = 3\text{ V}$ , $Z_S = Z_L = 50\ \Omega$ , $f = 1.8\text{ GHz}$ $f = 6\text{ GHz}$	$ S_{21e} ^2$	-	21.5 11	-	dB
Third order intercept point at output <sup>2)</sup> $V_{CE} = 3\text{ V}$ , $I_C = 30\text{ mA}$ , $Z_S = Z_L = 50\ \Omega$ , $f = 1.8\text{ GHz}$	$IP_3$	-	28	-	dBm
1dB Compression point at output $I_C = 30\text{ mA}$ , $V_{CE} = 3\text{ V}$ , $Z_S = Z_L = 50\ \Omega$ , $f = 1.8\text{ GHz}$	$P_{-1dB}$	-	13	-	

$$^1G_{ma} = |S_{21e} / S_{12e}| (k - (k^2 - 1)^{1/2}), G_{ms} = |S_{21e} / S_{12e}|$$

<sup>2</sup>IP3 value depends on termination of all intermodulation frequency components.  
Termination used for this measurement is  $50\ \Omega$  from 0.1 MHz to 6 GHz

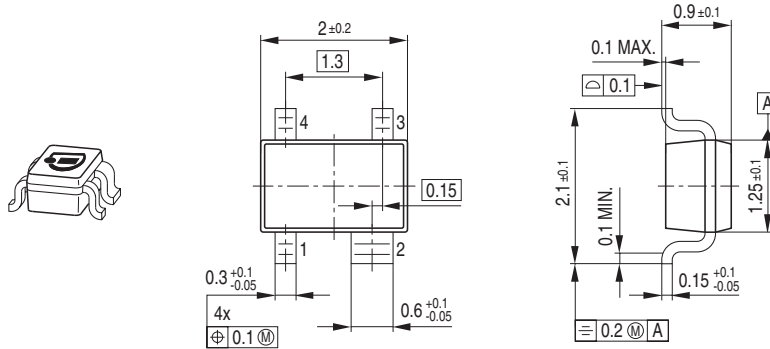
### **SPICE Parameter**

For the SPICE model as well as for S-parameters (including noise parameters) please refer to our internet website [www.infineon.com/rf.models](http://www.infineon.com/rf.models).

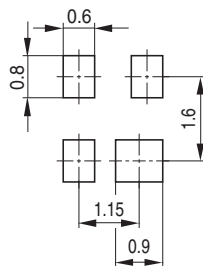
Please consult our website and download the latest versions before actually starting your design.

The simulation data have been generated and verified using typical devices. The BF776 SPICE model reflects the typical DC- and RF-performance with high accuracy.

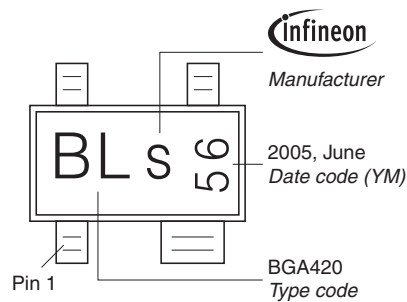
Package Outline



Foot Print

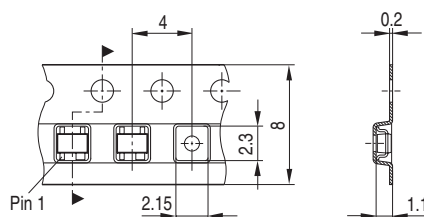


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel  
 Reel ø330 mm = 10.000 Pieces/Reel



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